

Please type a plus sign (+) inside this box →

+

PTO/SB/05 (12/97)

Approved for use through 09/30/00. OMB 0651-0032

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

**UTILITY
PATENT APPLICATION
TRANSMITTAL**

(Only for new non-provisional applications under 37 CFR 1.53(b))

Attorney Docket No.
95-0392.02

Total Pages

First Named Inventor or Application Identifier

Gurtej S. Sandhu and Sujit Sharan

Express Mail Label No.

EL003001756US

APPLICATION ELEMENTS

See MPEP chapter 600 concerning utility patent application contents.

ADDRESS TO:

Assistant Commissioner for Patents

Box Patent Application

Washington, DC 20231

1. ☒ Fee Transmittal Form
(Submit an original, and a duplicate for fee processing)
2. ☒ Specification Total Pages 20
(preferred arrangement set forth below)
-Descriptive
-Cross References to Related Application
-Statement Regarding Fed sponsored R & D
-Reference to Microfiche Appendix
-Background of the Invention
-Brief Summary of the Invention
-Brief Description of the Drawings (if filed)
-Detailed Description
-Claim(s)
-Abstract of the Disclosure
3. ☒ Drawing(s) (35 USC 113) Total Sheets 9
Total Pages 3
4. Oath or Declaration
a. ☐ Newly executed (original or copy)
b. ☒ Copy from a prior application (37CFR 1.63(d))
(for continuation/divisional with Box 17 completed)
[Note Box 5 below]
i. ☐ DELETION OF INVENTOR(S)
Signed statement attached deleting
inventor(s) named in the prior application,
see 37 CFR 1.63(d)(2) and 1.33(b).
5. ☐ Incorporation By Reference (useable if Box 4b is checked)
The entire disclosure of the prior application, from which a
copy of the oath or declaration is supplied under Box 4b,
is considered as being part of the disclosure of the
accompanying application and is hereby incorporated by
reference therein.

6. ☐ Microfiche Computer Program (Appendix)
7. Nucleotide and/or Amino Acid Sequence Submission
(if applicable, all necessary)
- a. ☐ Computer Readable Copy
b. ☐ Paper Copy (identical to computer copy)
c. ☐ Statement verifying identity of above copies

ACCOMPANYING APPLICATION PARTS

8. ☐ Assignment Papers (cover sheet & document(s))
9. ☒ 37 CFR 3.73(b) Statement ☒ Power of Attorney
(where there is an assignee)
10. ☐ English Translation Document (if applicable)
11. ☒ Information Disclosure ☒ Copies of IDS
Statement (IDS)/PTO-1449 Citations
12. ☒ Preliminary Amendment
13. ☒ Return Receipt Postcard (MPEP 503)
14. ☐ Small Entity ☐ Statement filed in prior application
Statement(s) Status still proper and desired
15. ☐ Certified Copy of Priority Document(s)
(if foreign priority is claimed)
16. ☐ Other

17. ☒ Continuation ☐ Divisional ☐ Continuation-in-part (CIP) of prior application No: ____/____

18. CORRESPONDENCE ADDRESS

- ☐ Customer Number or Bar Code Label ☐ Correspondence address below

(Insert Customer No. or Attach bar code label here)

NAME	Charles Brantley				
	Micron Technology, Inc.				
ADDRESS	8000 S. Federal Way				
	Mail Stop 525				
CITY	Boise	STATE	Idaho	ZIP CODE	83716
COUNTRY	USA	TELEPHONE	(208) 368-4557	Fax	(208) 368-5606

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Box Patent Application, Washington, DC 20231.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Gurtej S. Sandhu and Sujit Sharan

Serial No.:

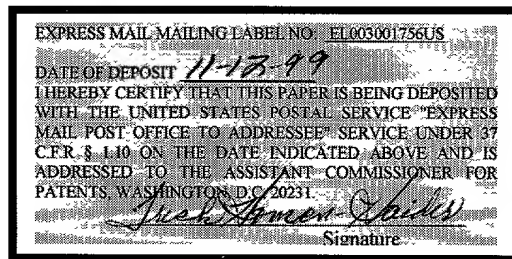
Filed: November 12, 1999

For: METHOD FOR IN-SITU CLEANING OF
INDUCTIVELY-COUPLED PLASMA CHAMBERS

§
§ Group Art Unit:
§
§ Examiner:
§
§ Atty. Docket: 95-0392.02
§
§
§
§

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

After awarding this application the benefit of the filing date of the parent application – serial number 08/795,379 filed February 4, 1997 – please amend the accompanying continuation application as follows:

IN THE DRAWINGS

Applicants note that the drawings submitted as part of this application are not the informal drawings originally submitted as part of the parent application. Rather, they are the formal drawings that were submitted at the end of prosecuting the parent application.

IN THE SPECIFICATION

In the title, please replace "METHOD" with --DEVICE--.

After the title, please include the following --

RELATED APPLICATION

This application is a continuation of pending United States Application Serial Number 08/795,379 filed February 4, 1997. --

On page 6, at the end of the section entitled DESCRIPTION OF THE FIGURES, please add

-- Figure 3 is a schematic drawing of another process chamber suitable for use with an exemplary embodiment of the current invention.--

On page 9, line 4, please replace "tertakis (diethylamino)" with -- tetrakis (dimethylamino) -- .

On page 11, line 23, after the sentence ending in "chambers." please add
-- In addition to the chamber depicted in figure 1, embodiments within the scope of the current invention apply to other types of processing chambers as well, including the one depicted in Figure 3. In that figure, system 100 includes a plasma generator 108 and a furnace tube 102. The furnace tube 102 comprises a ceramic shell 104 around a quartz tube 106 and is configured to hold substrate 20. Coupling the furnace tube 102 to a remote plasma chamber 40 allows for cleaning methods as described above.--

On page 20, in the Abstract, please complete the sentence ending on line 9 with -- chamber; and any conductive material is in-situ removed from the inside of the chamber to remove any blocking of the inductive power couple to the reaction chamber.--

IN THE CLAIMS

Please cancel claims 1-40.

Please add the following claims.

41. A plasma processing system, comprising:
- a first chamber configured to generate a first plasma therein; and
 - a second chamber coupled to said first chamber, wherein said second chamber is configured to initially generate a second plasma therein, further configured to lose an ability to generate said second plasma, and configured to receive said first plasma, wherein said first plasma is configured to restore said ability.
42. The system in claim 41, wherein said second chamber is configured to lose said ability in response to a generation of said second plasma, and further configured to regain said ability in response to a reception of said first plasma.
43. The system in claim 42, wherein said second chamber is a tube furnace.
44. The system in claim 43, wherein said first chamber is a tube furnace.
45. A furnace assembly, comprising:
- a structure defining a furnace interior, wherein at least a part of said structure is transparent to a radio-frequency wave, wherein said structure is configured to receive a first material that is opaque to said wave, and wherein said structure is configured to interpose between a source of said wave and said first material; and
 - a delivery system in fluid communication with said interior defined by said structure, said system configured to deliver a second material to said first material, wherein said second material is reactable with said first material.
46. The furnace assembly in claim 45, wherein said delivery system is configured to deliver an etchant.
47. The furnace assembly in claim 46, wherein said delivery system is configured to deliver a second material selected from a group comprising fluorine, chlorine, bromine, hydrogen chloride, hydrogen fluoride, hydrogen bromide, sulphur hexafluoride, nitrogen trifluoride, carbon tetrachloride (CCl₄), carbon tetrafluoride (CF₄), chlorine monofluoride (ClF), chlorine trifluoride

(ClF₃), bromine chloride (BrCl), bromine monofluoride (BrF), bromine trifluoride (BrF₃), bromine pentafluoride (BrF₅), iodine monobromide (IBr), iodine tribromide (IBr₃), iodine monochloride (ICl; alpha and beta), iodine trichloride (ICl₃), iodine pentafluoride (IF₅), iodine heptafluoride (IF₇), carbon dichlorodifluoride (CCl₂F₂), and NF₃.

48. The furnace assembly in claim 46, wherein said delivery system is configured to deliver a halogen.

49. The furnace assembly in claim 48, wherein said delivery system is configured to deliver a polyhalogen.

50. A semiconductor fabrication system, comprising:

a first reaction device configured to inductively generate a first plasma, wherein said first plasma comprises an induction blocker, and wherein said first reaction device is further configured to accept said induction blocker in an area that blocks plasma induction; and

a component coupled to said first reaction device and configured to provide said first reaction device with an induction blocker remover.

51. The semiconductor fabrication system in claim 50, wherein said component is a second reaction device configured to generate a second plasma comprising said induction blocker remover.

52. The semiconductor fabrication system in claim 51, wherein said first reaction device comprises a quartz component having an interior defining a plasma induction region; and wherein said quartz component is configured to accept said induction blocker thereon.

53. The semiconductor fabrication system in claim 52, wherein said second reaction device is configured to generate a second plasma comprising a conductive material remover.

54. A cleaning apparatus for an inductively-coupled plasma chamber, comprising:
a conduit configured to couple to said inductively-coupled plasma chamber; and
a cleaning chamber coupled to said conduit and configured to provide a metal-cleaning gas to said inductively-coupled plasma chamber through said conduit.
55. The cleaning apparatus of claim 54, further comprising a plasma-generation device around said cleaning chamber, wherein said plasma-generation device is configured to inductively generate a metal-etching plasma within said cleaning chamber.
56. The cleaning apparatus in claim 55, wherein said cleaning chamber is configured to provide said metal-etching plasma to said inductively-coupled plasma chamber through said conduit.
57. A wafer processing system, comprising:
a reactor having a wafer fabrication mode and a reactor cleaning mode, wherein said reactor is configured to receive a metal-containing gas during said wafer fabrication mode, locally generate a plasma during said wafer fabrication mode, receive a metal etchant during said reactor cleaning mode, and refrain from locally generating a plasma during said reactor cleaning mode; and
a chamber configured to couple to said reactor during said reactor cleaning mode and further configured to temporarily house said metal etchant.
58. The system in claim 57, wherein an interior of said reactor is free of any wafer during said reactor cleaning mode.
59. The system in claim 58, wherein said chamber is configured to transmit said metal etchant in a non-plasma form to said reactor during said cleaning mode.

60. A metal processing system, comprising:

a furnace comprising a quartz tube and configured to house a high-density plasma and to allow deposition of a metal on said quartz tube and on a wafer located inside said quartz tube; and

a cleaning chamber coupled to said furnace and configured to house a gas that is configured to etch said metal from said quartz tube.

61. The system in claim 60, wherein said furnace is configured to allow said gas to access said quartz tube to the exclusion of said wafer.

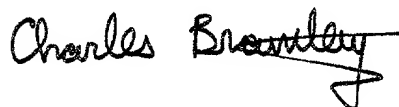
62. The system in claim 61, wherein said furnace is configured to allow said gas to access said quartz tube in response to a removal of said wafer from said furnace.

REMARKS

Claims 41-62 are pending. Applicants submit that they are allowable. If there are any matters that may be resolved or clarified through a telephone interview, the Examiner is requested to contact Applicants' undersigned attorney at the number indicated.

Respectfully submitted,

11/10/99



Charles Brantley
Registration No. 38,086
Micron Technology, Inc.
8000 S. Federal Way
Boise, ID 83716-9632
(208) 368-4557

Attorney for Applicants

CERTIFICATE OF EXPRESS MAILING

I HEREBY CERTIFY that this correspondence is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated below, in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, DC 20231.

DATE OF DEPOSIT: Feb. 4, 1997

EXPRESS MAIL LABEL NO: EM057349120US

Margaret M. Dunbar

Signature

Margaret M. Dunbar

Printed Name

PATENT APPLICATION
DOCKET NO. MICR154 (95-0392)

Method For In-situ Cleaning of Inductively-Coupled Plasma Chambers

INVENTORS:

Gurtej S. Sandhu

Sujit Sharan

Method For In-situ Cleaning of Inductively-Coupled Plasma Chambers

DESCRIPTION

BACKGROUND OF THE INVENTION

5

Technical Field. This invention relates to integrated circuit manufacturing processes and, more specifically, to a novel process for plasma fabrication procedures for semiconductor substrates using conductive materials.

Background. In order to build an integrated circuit, many active devices
10 need to be fabricated on a single substrate. The current practice in semiconductor manufacturing is to use thin film fabrication techniques. A large variety of materials can be deposited using thin films, including metals, semiconductors, insulators and the like. The composition and uniformity of these thin layers must be strictly controlled to facilitate etching of submicron features. The surface of the substrate, most often a wafer,
15 must be planarized in some way to prevent the surface topography from becoming increasingly rough with each added thin film level. The formation of such films is accomplished by a large variety of techniques.

Chemical vapor deposition (CVD) processes are often selected over competing deposition techniques because they offer numerous advantages, including the abilities of
20 CVD to deposit films from a wide variety of chemical compositions and provide improved conformality.

In general a CVD process includes the following steps: a selected composition and flow rate of reactant and inert gases are dispatched into a reaction chamber; the gases move to the substrate surface; the reactants are adsorbed on the substrate surface; the
25 species undergo a film-forming chemical reaction and the by-products of the reaction are desorbed from the surface and conveyed away from the surface.

Plasma enhanced CVD (PECVD) uses a plasma or glow discharge with a low pressure gas, to create free electrons which transfer energy into the reactant gases. This allows the substrate to remain at a lower temperature than in other CVD processes. A
30 lower substrate temperature is the major advantage of PECVD and provides film

deposition methods for substrates that do not have the thermal stability necessary for other processes that require higher temperature conditions. In addition, PECVD can enhance the deposition rate when compared to thermal reactions alone, and produce films of unique compositions and properties.

5 In most applications it is desired that thin films maintain a uniform thickness and freedom from cracks or voids. As thin films cross steps that occur on the surface of the underlying substrate, they often suffer unwanted deviations from the ideal conformality, such as thinning or cracking. A measure of how well a film maintains its nominal thickness is referred to as the step coverage of the film. The height of the step and the
10 aspect-ratio (the height-to-spacing ratio of two adjacent steps) of a feature being covered determine the expected step coverage. Step coverage of 100% is ideal, but normally a value less than 100% is specified as acceptable, for any given application.

The semiconductor industry's continuing drive towards closer and smaller device geometries, has placed an increased demand for cost-effective solutions for the problem
15 of higher step coverage and planarization. New plasma sources are being developed because traditional sources cannot extend to the sub-0.5 micron level of processing necessary for the more rigorous device geometries. Fabrication processes that are employed in response to the necessity of good conformality in the face of the submicron geometries include plasma enhanced directional sputtering, plasma enhanced etching and
20 plasma enhanced chemical vapor deposition. CVD processes have been developed for some metals, for example titanium and titanium nitride, both of which can be put to use in 0.35 and 0.25 micron devices. Because these typical back-end-of-the-line (BEOL) fabrication processes must be done at low temperatures (<450° C) to protect the integrity of previously deposited layers and to ensure that dopants don't diffuse excessively, they
25 are typically based on PECVD, which, as described above, can be achieved at low temperatures. These low temperature, high aspect ratio coverage PECVD process requirements are being met with low pressure, high density plasma (HDP) based processes. To achieve the good step coverage and gap fill desired, HDP CVD systems are run at a high flow rate to achieve adequate deposition. At the same time HDP CVD

process pressures need to be relatively low for the plasma to operate properly -- that is at high densities.

5 To deposit or etch conductive or metal films using HDP processes, the plasma must necessarily be generated using inductive coupling. The fabrication by deposition or removal of metal thin films in an inductively coupled high density plasma reactor is desirable because of the advantages it provides, including: lower processing temperatures and higher step coverage, as discussed above, as well as shorter processing times and denser films.

10 However, in the case of inductively coupled (IC) plasma procedures there is no capacitive coupling to the chamber walls, and any conductive material deposition on the chamber walls blocks the inductive power coupling to the plasma. For the deposition of conductive materials and metal films this means that the reactor chamber walls must be cleaned quite frequently in order to prevent the deposition of conductive materials on the chamber walls which blocks the IC plasma fabrication steps.

15 Traditionally the only way to remove ionic and metallic contaminants from any plasma reaction chamber or furnace tube has been to clean the tubes with wet etching, often with the simple method of manually rolling them, half submerged, in an acid bath. Cleaning of the reaction chamber in this manner involves removing the dirty quartz tube, installing a previously cleaned tube, and cleaning the dirty tube for future use. This method of cleaning is unsatisfactory for many reasons. Tearing down a furnace is a time consuming and difficult process that requires from 4-24 hours and has been likened to "open heart surgery". It requires not merely a tube change, but also a particle and process requalification of the furnace. The result is that any cleaning regime selected must balance the need to clean the furnace tube with the potential product yield loss and furnace downtime. In addition, a very significant disadvantage of any wet clean process is the increasingly strict regulatory controls placed on wet chemical disposal making it increasingly more costly and troublesome.

25 Several *in-situ* cleaning options exist for other CVD systems but metal and other conductive material contamination cannot be removed completely with any of the existing methods. Any conductive deposition on the chamber walls in an IC plasma

system blocks the power coupling to the plasma. The significance of this is that in the specific case of inductively coupled plasma chambers, since there is no capacitive coupling to the chamber walls, cleaning by generating a plasma containing an etchant gas to remove conductive material is not possible. With the growing need for more frequent
5 cleaning of furnace tubes, as is the case when using IC PECVD to deposit metals and conductive films an alternative cleaning method is still needed.

SUMMARY OF THE INVENTION

The present invention is a process for plasma enhanced fabrication of conductive
10 materials on a semiconductor substrate comprising the steps of placing the substrate in an inductively coupled (IC) plasma reaction chamber and maintaining the chamber under vacuum pressure while introducing at least a preselected reactant species gas, and optionally a carrier gas into the chamber for a preselected fabrication procedure on the substrate. A plasma is generated from the gas or gases within the chamber using a power
15 source inductively coupled to the reaction chamber. After the consequent fabrication procedure the substrate is removed from the chamber; and any conductive material is *in-situ* removed from the inside of the chamber to remove any blocking of the inductive power couple to the reaction chamber.

In one embodiment the *in-situ* removal of conductive material from the inside of
20 the reaction chamber is accomplished by the introduction of a remotely created plasma, which provides the necessary activated reactive species to carry out this step. The activated reactive species are created in a separate plasma reaction chamber, which is remote and separate from the inductively coupled PECVD chamber and then transported downstream and introduced into the reaction chamber to remove conductive material
25 from the inside of the reaction chamber.

In another embodiment the *in-situ* removal of conductive material is accomplished employing low temperature etching by the introduction of suitable etchant gases into the chamber. Suitable gases for etching the conductive materials, such as metals, contained in the fabrication step include, for example, compounds such as ClF_3 ,
30 other polyhalogen compounds or NF_3 .

Additional advantages and novel features of the invention will be set forth in part in the description that follows, and in part will become apparent to those skilled in the art upon examination of the following or may be learned by practice of the invention.

5

DESCRIPTION OF THE FIGURES

Figure 1 is a schematic drawing of an exemplary inductively coupled plasma-enhanced chemical vapor deposition chamber suitable for use with the process of this invention.

10 Figure 2 is a flow chart of the steps for the given embodiment of the process of this invention.

DETAILED DESCRIPTION

15 The present invention, broadly stated, is directed to plasma enhanced fabrication processes. The invented process permits the *in-situ* removal of conductive material from the inside of an inductively coupled plasma chamber. In general, for any fabrication procedure or step that utilizes a plasma or glow discharge in an inductively coupled reaction chamber and involves a conductive material, the selected fabrication step may be completed and followed by *in-situ* removal of conductive material from the inside of the inductively coupled plasma reaction chamber. Because of the nature of glow discharges or plasmas and conductive material, for example metals, such plasma enhanced processes must necessarily be carried out in an inductively coupled (IC) reaction chamber. The invention is particularly well-suited to processes that use metal-containing compounds and/or high density plasmas.

20 A plasma enhanced chemical vapor deposition (PECVD) process is described in detail to illustrate the utility of the process. The process is equally suited to any other process that uses a plasma in an inductively coupled reaction chamber and a conductive material. The exemplary embodiment using PECVD is not intended to limit the scope of the present invention to PECVD processes. Other appropriate processes for the present invention include, for example, plasma enhanced directional sputtering, etching of metals with high density plasma, surface conditioning treatments, and the like.

25
30

For PECVD metal film deposition in an IC chemical vapor deposition (CVD) reactor, the process of the invention, generally stated, includes the steps of: placing the substrate in a IC CVD reaction chamber under a preselected vacuum pressure; introducing a preselected composition of processing gas into the reaction chamber for metal deposition on the substrate; and generating a high density plasma from the gas within the reaction chamber using a power source inductively coupled to the reaction chamber; removing the substrate from the reaction chamber; and *in-situ* removal of conductive films from the inside of the chamber, to remove blocking of the inductive power couple to the reaction chamber. The *in-situ* chamber cleaning is accomplished by either introduction of activated reactive compounds , preferably contained in a remotely formed plasma for etching conductive materials or by introduction of gases for etching conductive materials.

The *in-situ* chamber cleaning process can be performed in any system for inductively coupled (IC) plasma enhanced (PE) fabrication processes. An IC high density plasma (HDP) system is described below and shown in FIG. 1 and is generally designated as 10. It is to be understood that the apparatus and embodiments described herein are meant to be a non-limiting examples to illustrate the process claimed in this invention.

A radio-frequency inductively coupled type of PECVD apparatus is provided with: a reaction chamber 12 that has a gas inlet port 14 in flow communication with a source, which is not shown, for supplying a metal precursor deposition gas 30 and a gas exhaust port 16 in flow communication with a source of vacuum for exhausting gas from chamber 12 and for maintaining a predetermined degree of vacuum therein. System 10 further includes a plasma generation means 22 arranged on an upper surface of reaction chamber 12; and a holder device 18 that holds a substrate 20, typically a semiconductor wafer, on which the metal deposition process step is performed in the plasma produced by the plasma generation means 22. Reaction chamber 12 is formed from an insulating material that is transparent to radio-frequency waves, for example quartz.

Plasma generation means 22 in this example includes a radio-frequency power source to three-turn antenna 26. Radio-frequency waves are generated inside reaction

chamber 12 from antenna 26, and metal precursor deposition gas 30 is activated by this electromagnetic energy to cause the generation of a plasma.

Optionally, as shown in figure 1, is a common configuration for holder device 18, here a susceptor, such that another radio-frequency power source 24 is connected thereto with a matching circuit 28 therebetween; radio-frequency electric power is supplied from this radio-frequency power source, and a self-bias potential is maintained with respect to the plasma's potential, via a blocking capacitor (not shown).

A source of conductive material, here metal precursor deposition gas 30, can be appropriately coupled to inlet port 14, through which deposition gas 30 is introduced into chamber 12. Optionally, a supply of carrier gas 32 can be added to metal precursor deposition gas 30 by inclusion of a suitable gas premix system that is likewise coupled to enter chamber 12 through suitable valving. Carrier gas 32 may include argon, helium and other suitable inert gases. With this arrangement inert carrier gas 32 and metal precursor deposition gas 30 can be combined prior to introduction into reaction chamber 12. The temperatures and flow rates of the gases can be controlled to achieve the desired reaction and film quality.

The flow rates of metal precursor deposition gas 30 and carrier gas 32 also have a significant effect on the deposited film. For a IC HDP reactor 10, as described above process temperatures in the range of 200° C. to 800° C. can be utilized. Process pressures for such an IC HDP reactor 10 may be in the range of 1 m Torr to 10 m Torr and with gas flow rates in the range of 100 to 800 sccm's (standard cubic centimeters per minute).

Power from radio-frequency power source 22, typically is in the range of 50 to 150 watts with a frequency of the order of 13.56 MHz. Radio-frequency waves are generated with reaction chamber 12 from antenna 26. This electromagnetic energy excites deposition gas 30 and optionally carrier gas 32, now resident in chamber 12 to form a plasma, and thus a high-density plasma of, for example, the order of 10^{10} to 10^{16} ions/cm³ is generated.

An example of a metal film that can be deposited using this process is titanium. In the deposition of a titanium metal film using this invention a desirable precursor deposition gas can be formed from titanium tetrachloride (TiCl₄). Argon can be used as a

carrier gas and bubbled through the TiCl_4 to form the gas. Alternatively, a precursor deposition gas for titanium may be selected from any suitable titanium source, including for example, titanium tetrabromide, titanium tetraiodide, tetrakis (diethylamino) titanium and tertakis (diethylamino) titanium.

5 The method of the invention is equally suitable for the deposition, conditioning, doping and etching of other metal and conductive films and suitable precursors for the selected fabrication reaction can be formed from an organic or inorganic metal source, as dictated by the characteristics desired in the selected fabrication step. In the titanium deposition example, substrate 20 is placed on holder 18 inside reaction chamber 12 and
10 vacuum pressure is established by a vacuum pump, not shown, that is in flow communication with exhaust port 16. The TiCl_4 , hydrogen and argon gas are then introduced into reaction chamber 12 through inlet port 14. A plasma is generated by application of radio-frequency power source 22, as described above and a metal film is formed on the surface of substrate 20. Substrate 20 is then removed from reaction
15 chamber 12 and any deposition of metal on the inside of reaction chamber 12 can then be removed *in-situ* to eliminate any blocking of the inductive power couple to reaction chamber 12. Chamber 12 is then ready for another substrate 20 for the selected fabrication procedure, here metal deposition.

 In one illustrative embodiment the *in-situ* removal of conductive material from the
20 inside of reaction chamber 12 is accomplished by the introduction of a remotely created plasma, which provides the necessary activated reactive species to carry out this step. Here reactive species includes ionized species and neutral species in high energy states. To accomplish this, the reactive species are created in separate plasma reaction chamber 40, which is remote and separate from inductively coupled PECVD chamber 12 and then
25 transported downstream and introduced into reaction chamber 12 to etch conductive material from the inside of chamber 12. This requires remote plasma chamber 40 to be in flow communication by way of inlet port 14 with reaction chamber 12. In the present example, the plasma for *in-situ* cleaning is generated in remote plasma chamber 40 and moved to reaction chamber 12 through conduit 13 to inlet port 14. The plasma
30 containing the reactive etchant species can be generated in remote plasma chamber 40, by

any suitable means to create the reactive species necessary for the *in-situ* cleaning step of the invention. Means for generating such a plasma are well known in the art and include, for example, a pair of oppositely placed electrodes, inductive coils, microwave sources, and other conductive and inductive power sources. In this example a plasma is the preferred means for creating the activated reactant species, but they can also be created using other suitable means, such as optical activation, thermal activation, ultrasonic activation and the like.

In another illustrative embodiment the *in-situ* removal of conductive material from the inside of reaction chamber 12 is accomplished employing low temperature etching by the introduction of suitable etchant gases into chamber 12 through inlet port 14. Suitable gases for etching the metals contained in the metal deposition step include, for example, compounds such as ClF_3 , other polyhalogen compounds or NF_3 . Additional examples of compounds suitable for etching the metals contained in the metal deposition step are listed elsewhere in this description.

In any embodiment the *in-situ* removal of conductive material from the inside of reaction chamber 12 is accomplished in the same manner after the preselected fabrication procedure. Whether the selected fabrication procedure is sputtering, etching or otherwise conditioning substrate 20, the selected fabrication step is then followed by *in-situ* cleaning of reaction chamber 12. For any preselected fabrication procedure the *in-situ* removal of conductive material from the inside surface of inductively coupled chamber 12 is accomplished by either introduction of a remotely formed plasma containing reactive compounds for etching conductive materials or by introduction of gases for etching conductive materials.

In any embodiment of the invention, after the *in-situ* removal of the conductive material from the inside of reaction chamber 12 has been accomplished, the etchant-containing species can then be pumped out of reaction chamber 12 through exhaust port 16. Likewise, in any embodiment the *in-situ* cleaning step may be considered to be performed as either a first step or last step in the metal deposition process claimed herein, as shown in Figure 2.

Turning now to the etchant gas sources for the *in-situ* cleaning step in any embodiment of the inventive process, they can be provided in any form that produces the desirable reactive species relative to the metal or conductive material that needs to be removed from the inside of chamber 12 in order to remove any blocking of the inductive power couple to reaction chamber 12. Typical examples of suitable etchant compounds include fluorine, chlorine, bromine, hydrogen chloride, hydrogen fluoride, hydrogen bromide, sulphur hexafluoride, nitrogen trifluoride, carbon tetrachloride (CCl₄), carbon tetrafluoride (CF₄), chlorine monofluoride (ClF), chlorine trifluoride (ClF₃), bromine chloride (BrCl), bromine monofluoride (BrF), bromine trifluoride (BrF₃), bromine pentafluoride (BrF₅), iodine monobromide (IBr), iodine tribromide (IBr₃), iodine monochloride (ICl; alpha and beta), iodine trichloride (ICl₃), iodine pentafluoride (IF₅), iodine heptafluoride (IF₇), carbon dichlorodifluoride (CCl₂F₂), other halogen and polyhalogen compounds and the like. The etchant source gases can be provided in either a gas phase or as liquid source converted to the gas phase through a bubbler system.

In conclusion, this plasma enhanced method for fabrication procedures that involve conductive material, using an inductively coupled plasma chamber with *in-situ* cleaning of the reaction chamber provides many advantages. These advantages include, for example, improved film condition and quality, in terms of step coverage, film density and multi-layer integrity. This invention provides a method for fabrication procedures for semiconductor substrates involving conductive material and employing a plasma for the smaller geometries that are now crucial to device functionality. This invention allows inductively coupled plasma chambers to be cleaned without dismantling, re-assembling and recertifying the plasma chambers. Other examples of the advantages provided by this invention include higher system throughput and reduced chemical disposal costs and other economic benefits.

It is intended that alternate embodiments of the inventive concepts are possible without departing from the scope of the invention as expressed in the following claims.

We claim:

1 1. A method of *in-situ* cleaning an inductively coupled plasma reaction chamber, the
2 method comprising introducing remotely formed, preselected activated reactant species
3 into the reaction chamber.

1 2. A method of *in-situ* cleaning an inductively coupled plasma reaction chamber, the
2 method comprising introducing gases which contain preselected reactant species into the
3 reaction chamber.

1 3. A method for plasma enhanced fabrication of a semiconductor substrate in an
2 inductively coupled plasma reaction chamber, said chamber having an inside surface, the
3 method comprising the steps of:
4 contacting the substrate with a plasma containing preselected reactant species for
5 a preselected fabrication step;
6 removing the substrate from the reaction chamber after the fabrication step;
7 removing deposited material *in-situ* from the inside surface of the inductively
8 coupled plasma reaction chamber by introducing remotely formed, preselected activated
9 reactant species into the reaction chamber.

1 4. The method of Claim 3 wherein the preselected fabrication step is plasma
2 enhanced sputtering.

1 5. The method of Claim 3 wherein the preselected fabrication step is plasma
2 enhanced etching.

1 6. The method of Claim 3 wherein the preselected fabrication step is plasma
2 enhanced chemical vapor deposition.

1 7. The method of Claim 3 wherein the plasma is a high density plasma.

1 8. A method for plasma enhanced fabrication of a semiconductor substrate in an
2 inductively coupled plasma reaction chamber, said chamber having an inside surface, the
3 method comprising the steps of:
4 contacting the substrate with a plasma containing preselected reactant species for
5 a preselected fabrication step;
6 removing the substrate from the reaction chamber after the fabrication step;
7 removing deposited material *in-situ* from the inside surface of the inductively
8 coupled plasma reaction chamber by introducing gases which contain preselected reactant
9 species into the reaction chamber.

1 9. The method of Claim 8 wherein the preselected fabrication step is plasma
2 enhanced sputtering.

1 10. The method of Claim 8 wherein the preselected fabrication step is plasma
2 enhanced etching.

1 11. The method of Claim 8 wherein the preselected fabrication step is plasma
2 enhanced chemical vapor deposition.

1 12. The method of Claim 8 wherein the plasma is a high density plasma.

1 13. A method for PECVD deposition of metal films on a substrate in an inductively
2 coupled (IC) plasma enhanced chemical vapor deposition (PECVD) reactor comprising:
3 placing the substrate in the inductively coupled PECVD reaction chamber having
4 an inside and an outside;

5 maintaining the reaction chamber under vacuum pressure;

6 introducing at least a metal precursor deposition gas into the reaction chamber for
7 metal deposition on the substrate;

8 generating a plasma from the gas within the reaction chamber using a power
9 source inductively coupled to the reaction chamber;

10 removing the substrate from reaction chamber; and

11 *in-situ* removing deposited material from the inside of the chamber to remove any
12 blocking of the inductive power couple to the reaction chamber.

1 14. The method of Claim 13 wherein the plasma generated in the reaction chamber is
2 a high density plasma.

1 15. The method of Claim 13 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber a chemical species generated in a remotely
3 formed plasma for etching the material.

1 16. The method of Claim 13 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber remotely formed activated reactant species for
3 etching the material.

1 17. The method of Claim 13 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber gases for etching the material.

1 18. The method of Claim 13 wherein the vacuum pressure maintained in the reaction
2 chamber is in the range of 1 to 10 mtorr.

1 19. The method of Claim 14 wherein the vacuum pressure maintained in the reaction
2 chamber is in the range of 1 to 10 mtorr.

1 20. The method of Claim 15 wherein the vacuum pressure maintained in the reaction
2 chamber is in the range of 1 to 10 mtorr.

1 21. The method of Claim 16 wherein the vacuum pressure maintained in the reaction
2 chamber is in the range of 1 to 10 mtorr.

1 22. The method of Claim 17 wherein the vacuum pressure maintained in the reaction
2 chamber is in the range of 1 to 10 mtorr.

1 23. A semiconductor device produced by the process comprising the steps of:
2 placing a substrate in an inductively coupled chemical vapor deposition chamber
3 having an inside and an outside;
4 maintaining the chamber under vacuum pressure;
5 introducing a metal precursor deposition gas and a carrier gas into the chamber for
6 metal deposition on the substrate;

7 generating a plasma from the gases in the chamber using a power source
8 inductively coupled to the reaction chamber;
9 removing the substrate from reaction chamber; and
10 *in-situ* removing of deposited material from the inside of the chamber to remove
11 any blocking of the inductive power couple to the reaction chamber.

1 24. The device of Claim 23 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber a chemical species generated in a remotely
3 formed plasma for etching the material.

1 25. The method of Claim 23 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber remotely formed activated reactant species for
3 etching the material.

1 26. The device of Claim 23 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber gases for etching the material.

1 27. A method of forming a metal layer on a semiconductor wafer, using an
2 inductively coupled, plasma enhanced chemical vapor deposition chamber, the method
3 comprising the steps of:
4 forming a plasma containing a metal precursor deposition gas; exposing the wafer
5 to the plasma sufficiently to deposit a metal layer thereon; removing the wafer from the
6 chamber and *in-situ* cleaning the chamber to remove any material blocking the inductive
7 couple to the chamber.

1 28. The method of Claim 27 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber a remotely formed
3 plasma containing chemicals for etching the material.

1 29. The method of Claim 27 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber gases for etching the
3 material.

1 30. A method of altering a substantially planar surface on a semiconductor wafer,
2 using an inductively coupled, plasma chamber, the method comprising the steps of:
3 forming a plasma containing a reactant conductive material gas; exposing the
4 wafer to the plasma sufficiently to alter a surface layer thereon; removing the wafer from
5 the chamber and *in-situ* cleaning the chamber to remove any material blocking the
6 inductive couple to the chamber.

1 31. The method of Claim 30 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber a remotely formed
3 plasma containing chemicals for etching the material.

1 32. The method of Claim 30 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber gases for etching the
3 material.

1 33. A method of making a semiconductor device, comprising the steps of:

2 exposing a substrate to products formed in an inductively coupled plasma chamber
3 through the interaction of a noble gas plasma and a reactant-species-forming compound
4 to alter a metal layer on at least a portion of the substrate, *in-situ* removal of deposited
5 material from the chamber.

1 34. The method of Claim 33 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber a chemical species generated in a remotely
3 formed plasma for etching the material.

1 35. The method of Claim 33 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber remotely formed activated reactant species for
3 etching the material.

1 36. The method of Claim 33 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber gases for etching the
3 material.

1 37. A method of making a semiconductor device, comprising the steps of:
2 exposing a substrate to products formed in an inductively coupled plasma chamber
3 through the interaction of a noble gas plasma and reactant-species-forming compound to
4 alter a surface on at least a portion of the substrate, *in-situ* removal of deposited material
5 from the chamber.

1 38. The method of Claim 37 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber a chemical species generated in a remotely
3 formed plasma for etching the material.

1 39. The method of Claim 37 wherein the *in-situ* removing of material is accomplished
2 by introducing into the reaction chamber remotely formed activated reactant species for
3 etching the material.

1 40. The method of Claim 37 wherein the *in-situ* removing of material from the
2 chamber is accomplished by introducing into the reaction chamber gases for etching the
3 material.

Variable	Mean	SD	Min	Max
Age	38.5	10.5	25	55
Gender	Male	Female		
Marital status	Married	Single		
Education	High school	College		
Occupation	Manager	Worker		
Income	Low	High		
Health status	Good	Poor		
Stress level	Low	High		
Life satisfaction	Low	High		
Depression	Low	High		
Loneliness	Low	High		
Self-esteem	Low	High		
Resilience	Low	High		
Optimism	Low	High		
Gratitude	Low	High		
Forgiveness	Low	High		
Empathy	Low	High		
Compassion	Low	High		
Kindness	Low	High		
Generosity	Low	High		
Patience	Low	High		
Humility	Low	High		
Modesty	Low	High		
Shyness	Low	High		
Introversion	Low	High		
Extroversion	Low	High		
Sensitivity	Low	High		
Emotionality	Low	High		
Impulsivity	Low	High		
Risk-taking	Low	High		
Curiosity	Low	High		
Openness	Low	High		
Conscientiousness	Low	High		
Agreeableness	Low	High		
Neuroticism	Low	High		
Stability	Low	High		
Control	Low	High		
Power	Low	High		
Authority	Low	High		
Leadership	Low	High		
Influence	Low	High		
Impact	Low	High		
Significance	Low	High		
Importance	Low	High		
Value	Low	High		
Meaning	Low	High		
Purpose	Low	High		
Goal	Low	High		
Direction	Low	High		
Focus	Low	High		
Attention	Low	High		
Concentration	Low	High		
Effort	Low	High		
Perseverance	Low	High		
Determination	Low	High		
Resolve	Low	High		
Willpower	Low	High		
Strength	Low	High		
Power	Low	High		
Influence	Low	High		
Impact	Low	High		
Significance	Low	High		
Importance	Low	High		
Value	Low	High		
Meaning	Low	High		
Purpose	Low	High		
Goal	Low	High		
Direction	Low	High		
Focus	Low	High		
Attention	Low	High		
Concentration	Low	High		
Effort	Low	High		
Perseverance	Low	High		
Determination	Low	High		
Resolve	Low	High		
Willpower	Low	High		
Strength	Low	High		

5

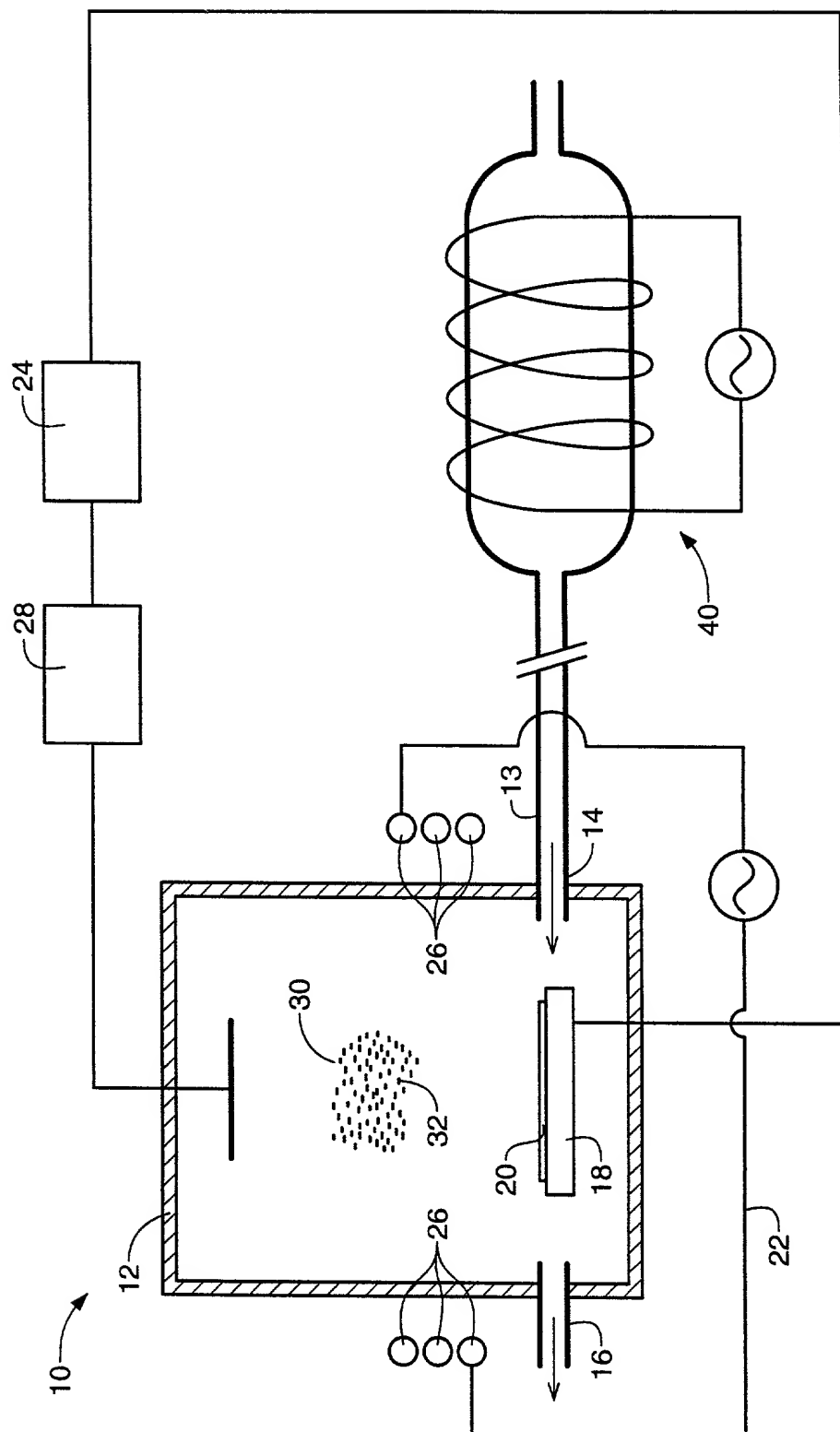


FIG. 1

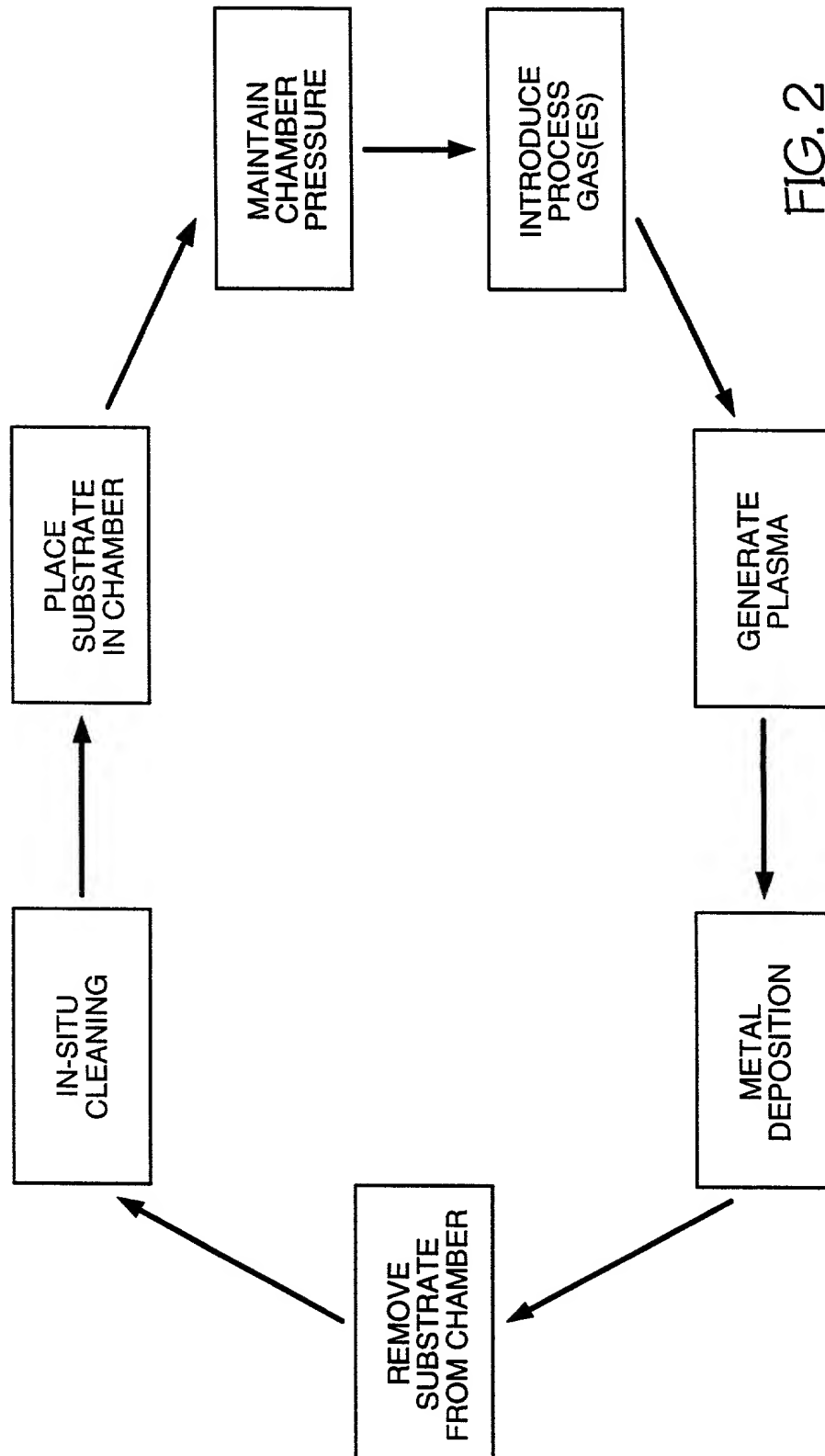


FIG. 2

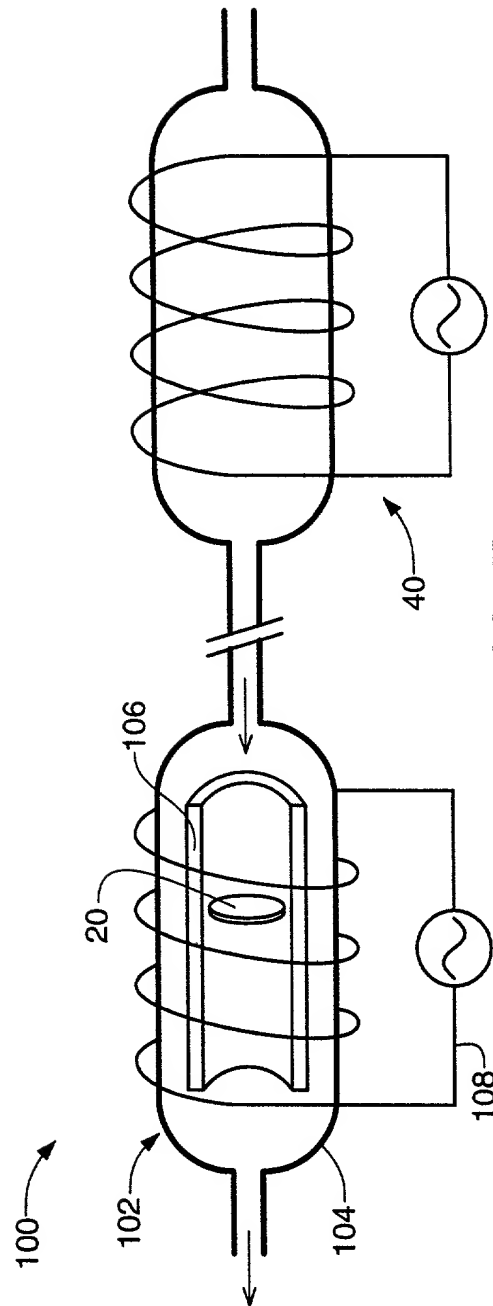


FIG. 3

Type a plus sign (+) inside this box →



Approved for use through
Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

PTO/SB/xx (6-95)
OMB 0651-0032

0010/PTO
Rev. 6/95

U.S. Department of Commerce
Patent and Trademark Office

DECLARATION

☒ Declaration Submitted with Initial Filing OR ☐ Declaration Submitted after Initial Filing

Attorney Docket Number

MICR154(95-0392)

First Named Inventor

Gurtej S. Sandhu

COMPLETE IF KNOWN

Application Number

Filing Date

February 4, 1997

Group Art Unit

Examiner Name

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

Method For In-situ Cleaning of Inductively-Coupled Plasma Chambers

the specification of which

(Title of the invention)

☒ is attached hereto

OR

☐ was filed on (MM/DD/YYYY)

as United States Application Number or PCT International

Application Number

and was amended on (MM/DD/YYYY)

(if applicable).

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment specifically referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37 Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119 (a)-(d) or § 365(b) of any foreign application(s) for patent or inventor's certificate, or § 365 (a) of any PCT international application which designated at least one country other than the United States of America, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or of any PCT international application having a filing date before that of the application on which priority is claimed.

Prior Foreign Application Number(s)	Country	Foreign Filing Date (MM/DD/YYYY)	Priority Not Claimed	Copy Attached?	
				YES	NO
			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

☐ Additional foreign application numbers are listed on a supplemental priority sheet attached hereto:

I hereby claim the benefit under Title 35, United States Code § 119(e) of any United States provisional application(s) listed below

Application Number(s)	Filing Date (MM/DD/YYYY)	<input type="checkbox"/> Additional provisional application numbers are listed on a supplemental priority sheet attached hereto.

Burden Hour Statement: This form is estimated to take .4 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231, and to the Office of Information and Regulatory Affairs, Office of Management and Budget (Project 0651-0032), Washington DC 20503. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

DECLARATION

Page 2

I hereby claim the benefit under Title 35, United States Code § 120 of any United States application(s), or § 365(c) of any PCT international application designating the United States of America, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code § 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

U.S. Parent Application Number	PCT Parent Number	Parent Filing Date (MM/DD/YYYY)	Parent Patent Number (if applicable)

☐ Additional U.S. or PCT international application numbers are listed on a supplemental priority sheet attached hereto.

As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

Firm Name Ormiston, Korfanta, Dunbar & Holland, P.L.L.C.

Payor Number (if applicable)

Name	Registration Number	Name	Registration Number
Margaret M. Dunbar	37,818	Lia M. Pappas	34,095
Craig M. Korfanta	33,255	Michael L. Lynch	30,871
Steven R. Ormiston	35,974		
Joseph W. Holland	38,919		

☐ Additional attorney(s) and/or agent(s) named on a supplemental sheet attached hereto.

☒ Please direct all correspondence to: Name Margaret M. Dunbar

Address P.O. Box 1840

Address

City Boise State ID ZIP 83701-1840

Country U.S.A Telephone (208) 336-1234 Fax (208) 336-8344

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Name of Sole or First Inventor:

☐ A petition has been filed for this unsigned inventor

Given Name Gurtej Middle Initial S. Family Name Sandhu Suffix

Inventor's Signature Gurtej Singh Sandhu Date Jan 30, 1997

RESIDENCE: City Boise State ID Country U.S.A. Citizenship U.K.

POST OFFICE ADDRESS 2964 E. Parkriver Dr.

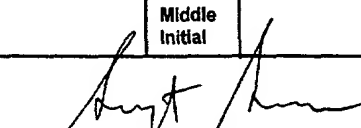
City Boise State ID Zip 83706 Country U.S.A. Applicant Authority

☒ Additional inventors are being named on supplemental sheet(s) attached hereto

Type a plus sign (+) inside this box --> ☐

DECLARATION

ADDITIONAL INVENTOR(S) Supplemental Sheet

Name of Additional Joint Inventor, if any:										<input type="checkbox"/> A petition has been filed for this unsigned inventor													
Given Name		Sujit			Middle Initial					Family Name		Sharan			Suffix								
Inventor's Signature												Date		1/30/97									
RESIDENCE: City		Boise			State		ID			Country		U.S.A			Citizenship		India						
POST OFFICE ADDRESS				5683 S. Alyssum Place																			
City		Boise			State		ID			Zip		83705			Country		U.S.A			Applicant Authority			
Name of Additional Joint Inventor, if any:										<input type="checkbox"/> A petition has been filed for this unsigned inventor													
Given Name					Middle Initial					Family Name					Suffix								
Inventor's Signature												Date											
RESIDENCE: City					State					Country					Citizenship								
POST OFFICE ADDRESS																							
City					State					Zip					Country					Applicant Authority			
Name of Additional Joint Inventor, if any:										<input type="checkbox"/> A petition has been filed for this unsigned inventor													
Given Name					Middle Initial					Family Name					Suffix								
Inventor's Signature												Date											
RESIDENCE: City					State					Country					Citizenship								
POST OFFICE ADDRESS																							
City					State					Zip					Country					Applicant Authority			
Name of Additional Joint Inventor, if any:										<input type="checkbox"/> A petition has been filed for this unsigned inventor													
Given Name					Middle Initial					Family Name					Suffix								
Inventor's Signature												Date											
RESIDENCE: City					State					Country					Citizenship								
POST OFFICE ADDRESS																							
City					State					Zip					Country					Applicant Authority			
Name of Additional Joint Inventor, if any:										<input type="checkbox"/> A petition has been filed for this unsigned inventor													
Given Name					Middle Initial					Family Name					Suffix								
Inventor's Signature												Date											
RESIDENCE: City					State					Country					Citizenship								
POST OFFICE ADDRESS																							
City					State					Zip					Country					Applicant Authority			
Additional inventors are being named on supplemental sheet(s) attached hereto										<input type="checkbox"/>													

Atty. Docket: 95-0392.02

~~~~~

EXPRESS MAIL MAILING LABEL NO.: EL003001756US

DATE OF DEPOSIT 11-13-99  
I HEREBY CERTIFY THAT THIS PAPER IS BEING DEPOSITED WITH THE  
UNITED STATES POSTAL SERVICE "EXPRESS MAIL POST OFFICE TO  
ADDRESSEE" SERVICE UNDER 37 C.F.R. § 1.110 ON THE DATE INDICATED  
ABOVE AND IS ADDRESSED TO THE ASSISTANT COMMISSIONER FOR  
PATENTS, WASHINGTON, D.C. 20231

*Trish Jordan-Walker*  
Signature

Dear Sir:

The undersigned, being Assignee of the entire interest in the above-identified application by virtue of an Assignment recorded in the United States Patent and Trademark Office as set forth below or filed herewith, hereby elects, under 37 C.F.R. § 3.71, to prosecute the application to the exclusion of the inventor(s).

The Assignee hereby revokes any previous Powers of Attorney and appoints: Charles B. Brantley, II, Reg. No. 38,086; Michael L. Lynch, Reg. No. 30,871; Lia M. Pappas, Reg. No. 34,095; Walter D. Fields, Reg. No. 37,130; Kevin D. Martin, Reg. No. 37,882; and David J. Paul, Reg. No. 34,692 as its attorney or agent, with full power of substitution and revocation, to prosecute the application, to make alterations and amendments therein, to transact all business in the Patent and Trademark Office in connection therewith, to receive any Letters Patent, and for one year after issuance of such Letters Patent to file any request for a certificate of correction that may be deemed appropriate.

Pursuant to 37 C.F.R. § 3.73, the undersigned duly authorized designee of Assignee certifies that the evidentiary documents have been reviewed, specifically the Assignment to MICRON TECHNOLOGY, INC. referenced below, and certifies that to the best of my knowledge and belief, title remains in the name of the Assignee.

Please direct all communications as follows:

       Filed concurrently herewith for  
recording, a copy of which is  
attached hereto.

X Previously recorded on: 2/4/97,  
at Reel: 8467 Frame: 0050 .

**Charles Brantley**  
**MICRON TECHNOLOGY, INC.**  
8000 S. Federal Way  
Mail Stop 525  
Boise, ID 83716-9632  
(208) 368-4557

ASSIGNEE: MICRON TECHNOLOGY, INC.

Date: Apr 11, 1999

By: Michael L. Lynch  
Michael L. Lynch, Reg. No. 30,871  
Chief Patent Counsel